

H11D1M, H11D2M, H11D3M, 4N38M, MOC8204M High Voltage Phototransistor Optocouplers

Features

- High voltage:
 - MOC8204M, $BV_{CER} = 400V$
 - H11D1M, H11D2M, $BV_{CER} = 300V$
 - H11D3M, $BV_{CER} = 200V$
- High isolation voltage:
 - 7500 V_{AC} peak, 1 second
- Underwriters Laboratory (UL) recognized
File # E90700, Volume 2

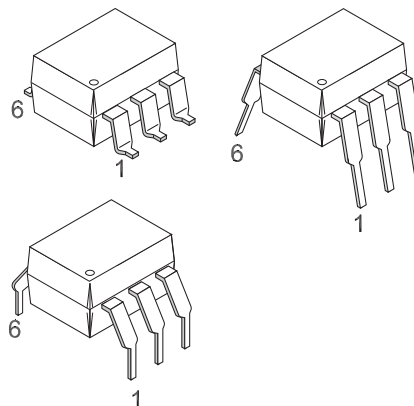
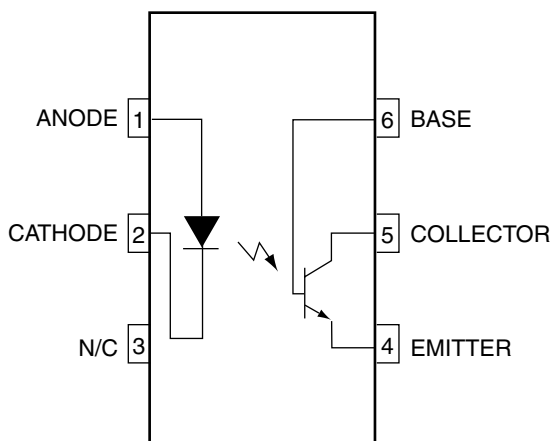
Applications

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs
- Appliance sensor systems
- Industrial controls

General Description

The H11DXM, 4N38M and MOC8204M are photo-transistor-type optically coupled optoisolators. A gallium arsenide infrared emitting diode is coupled with a high voltage NPN silicon phototransistor. The device is supplied in a standard plastic six-pin dual-in-line package.

Schematic



Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Device	Value	Units
TOTAL DEVICE				
T _{STG}	Storage Temperature	All	-55 to +150	°C
T _{OPR}	Operating Temperature	All	-40 to +100	°C
T _{SOL}	Lead Solder Temperature (Wave Solder)	All	260 for 10 sec	°C
P _D	Total Device Power Dissipation @ T _A = 25°C Derate Above 25°C	All	260	mW
			3.5	mW/°C
EMITTER				
I _F	Forward DC Current ⁽¹⁾	All	80	mA
V _R	Reverse Input Voltage ⁽¹⁾	All	6.0	V
I _F (pk)	Forward Current – Peak (1µs pulse, 300pps) ⁽¹⁾	All	3.0	A
P _D	LED Power Dissipation @ T _A = 25°C ⁽¹⁾ Derate Above 25°C	All	150	mW
			1.41	mW/°C
DETECTOR				
P _D	Power Dissipation @ T _A = 25°C Derate linearly above 25°C	All	300	mW
			4.0	mW/°C
V _{CER}	Collector to Emitter Voltage ⁽¹⁾	MOC8204M	400	V
		H11D1M, H11D2M	300	
		H11D3M	200	
		4N38M	80	
V _{CBO}	Collector Base Voltage ⁽¹⁾	MOC8204M	400	V
		H11D1M, H11D2M	300	
		H11D3M	200	
		4N38M	80	
V _{ECO}	Emitter to Collector Voltage ⁽¹⁾	H11D1M, H11D2M, H11D3M, MOC8204M	7	V
I _C	Collector Current (Continuous)	All	100	mA

Note:

- Parameters meet or exceed JEDEC registered data (for 4N38M only).

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified.)**Individual Component Characteristics**

Symbol	Characteristic	Test Conditions	Device	Min.	Typ.*	Max.	Unit
EMITTER							
V_F	Forward Voltage ⁽²⁾	$I_F = 10\text{mA}$	All		1.15	1.5	V
$\frac{\Delta V_F}{\Delta T_A}$	Forward Voltage Temp. Coefficient		All		-1.8		mV/°C
BV_R	Reverse Breakdown Voltage	$I_R = 10\mu\text{A}$	All	6	25		V
C_J	Junction Capacitance	$V_F = 0\text{V}, f = 1\text{MHz}$	All		50		pF
		$V_F = 1\text{V}, f = 1\text{MHz}$			65		pF
I_R	Reverse Leakage Current ⁽²⁾	$V_R = 6\text{V}$	All		0.05	10	μA
DETECTOR							
BV_{CER}	Breakdown Voltage Collector to Emitter ⁽²⁾	$R_{BE} = 1\text{M}\Omega, I_C = 1.0\text{mA}, I_F = 0$	MOC8204M	400			V
			H11D1M/2M	300			
			H11D3M	200			
BV_{CEO}		No R_{BE} , $I_C = 1.0\text{mA}$	4N38M	80			
BV_{CBO}	Collector to Base ⁽²⁾	$I_C = 100\mu\text{A}, I_F = 0$	MOC8204M	400			V
			H11D1M/2M	300			
			H11D3M	200			
			4N38M	80			
BV_{EBO}	Emitter to Base	$I_E = 100\mu\text{A}, I_F = 0$	4N38M	7			V
BV_{ECO}	Emitter to Collector	$I_E = 100\mu\text{A}, I_F = 0$	All	7	10		V
I_{CER}	Leakage Current Collector to Emitter ⁽²⁾ ($R_{BE} = 1\text{M}\Omega$)	$V_{CE} = 300\text{V}, I_F = 0, T_A = 25^\circ\text{C}$	MOC8204M			100	nA
		$V_{CE} = 300\text{V}, I_F = 0, T_A = 100^\circ\text{C}$				250	μA
		$V_{CE} = 200\text{V}, I_F = 0, T_A = 25^\circ\text{C}$	H11D1M/2M			100	nA
		$V_{CE} = 200\text{V}, I_F = 0, T_A = 100^\circ\text{C}$				250	μA
		$V_{CE} = 100\text{V}, I_F = 0, T_A = 25^\circ\text{C}$	H11D3M			100	nA
		$V_{CE} = 100\text{V}, I_F = 0, T_A = 100^\circ\text{C}$				250	μA
I_{CEO}		No R_{BE} , $V_{CE} = 60\text{V}, I_F = 0, T_A = 25^\circ\text{C}$	4N38M			50	nA

Transfer Characteristics ($T_A = 25^\circ\text{C}$ Unless otherwise specified.)

Symbol	Characteristics	Test Conditions	Device	Min.	Typ.*	Max.	Units
EMITTER							
CTR	Current Transfer Ratio, Collector to Emitter	$I_F = 10\text{mA}, V_{CE} = 10\text{V}, R_{BE} = 1\text{M}\Omega$	H11D1M/2M/3M, MOC8204M	2 (20)			mA (%)
		$I_F = 10\text{mA}, V_{CE} = 10\text{V}$	4N38M	2 (20)			
$V_{CE(\text{SAT})}$	Saturation Voltage ⁽²⁾	$I_F = 10\text{mA}, I_C = 0.5\text{mA}, R_{BE} = 1\text{M}\Omega$	H11D1M/2M/3M, MOC8204M		0.1	0.40	V
		$I_F = 20\text{mA}, I_C = 4\text{mA}$	4N38M			1.0	
SWITCHING TIMES							
t_{ON}	Non-Saturated Turn-on Time	$V_{CE} = 10\text{V}, I_{CE} = 2\text{mA}, R_L = 100\Omega$	All		5		μs
t_{OFF}	Turn-off Time		All		5		μs

*All Typical values at $T_A = 25^\circ\text{C}$ **Note:**

2. Parameters meet or exceed JEDEC registered data (for 4N38M only).

DC Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified.) (Continued)**Isolation Characteristics**

Symbol	Characteristic	Test Conditions	Device	Min.	Typ.*	Max.	Units
V_{ISO}	Isolation Voltage	$f = 60\text{Hz}$, $t = 1 \text{ sec.}$	All	7500			V_{ACPEAK}
R_{ISO}	Isolation Resistance	$V_{\text{I-O}} = 500 \text{ VDC}$	All	10^{11}			Ω
C_{ISO}	Isolation Capacitance	$f = 1\text{MHz}$	All		0.2		pF

*All Typical values at $T_A = 25^\circ\text{C}$

Typical Performance Curves

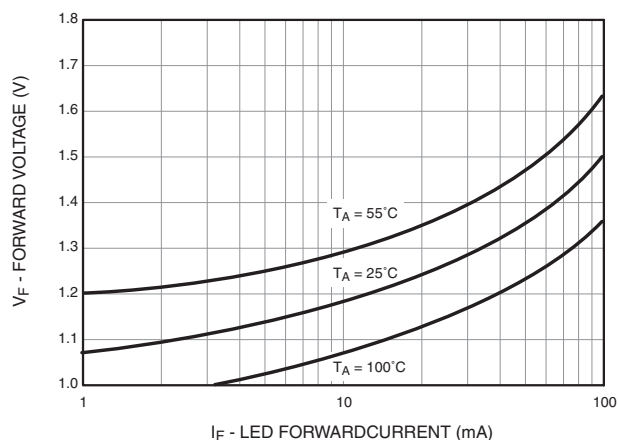


Fig. 1 LED Forward Voltage vs. Forward Current

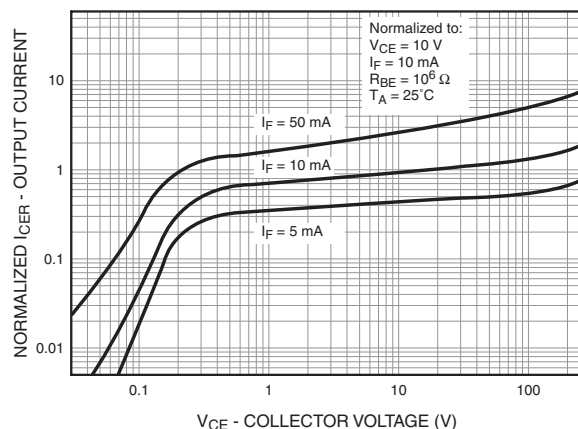


Fig. 2 Normalized Output Characteristics

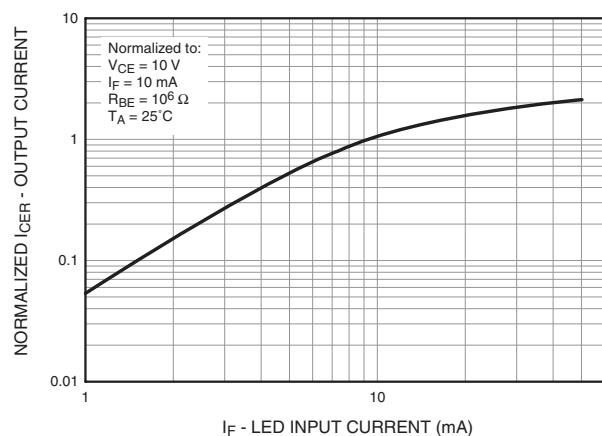


Fig. 3 Normalized Output Current vs. LED Input Current

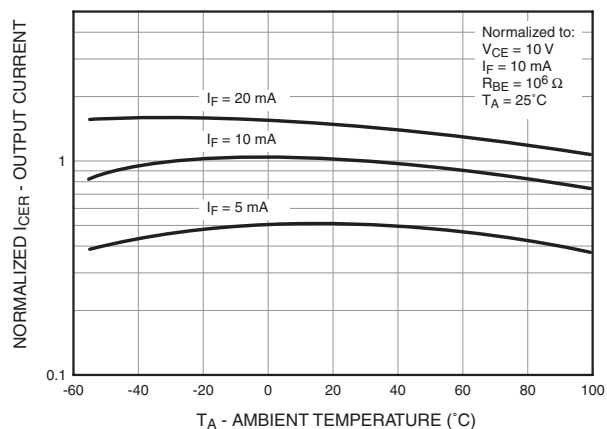


Fig. 4 Normalized Output Current vs. Temperature

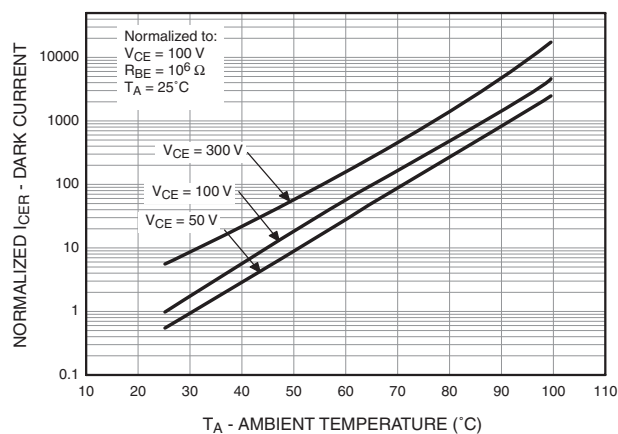


Fig. 5 Normalized Dark Current vs. Ambient Temperature

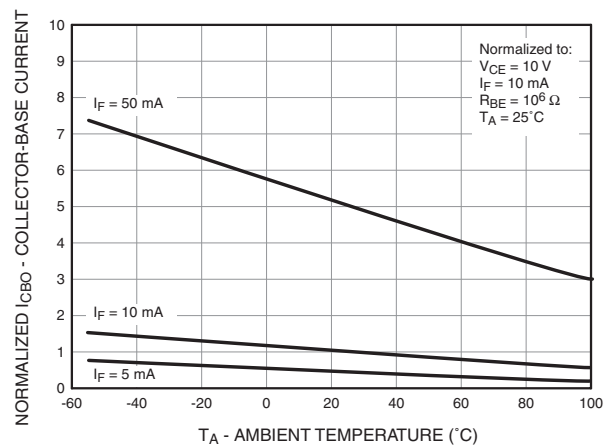
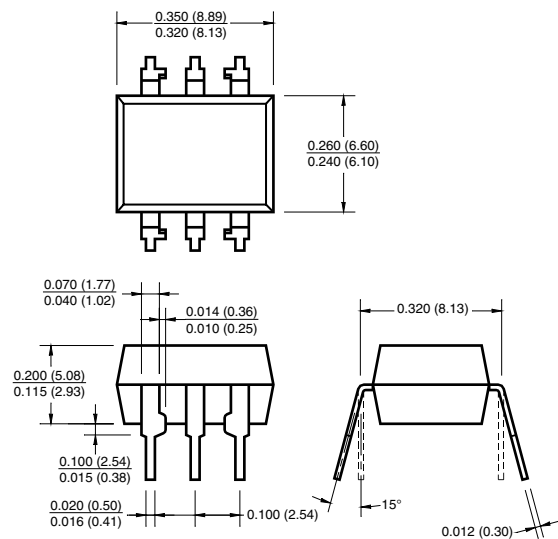


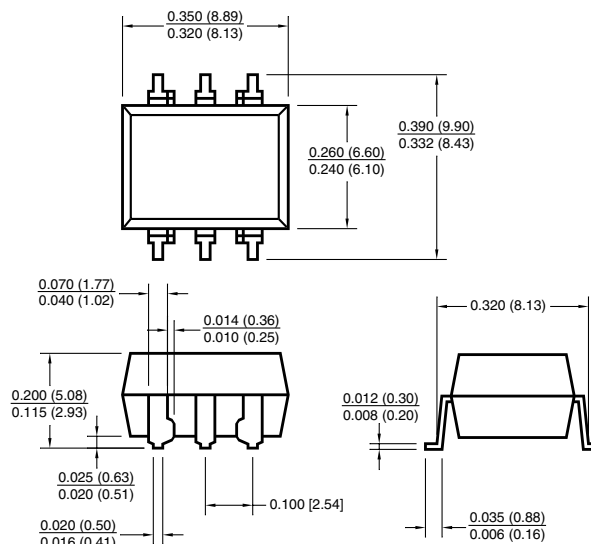
Fig. 6 Normalized Collector-Base Current vs. Temperature

Package Dimensions

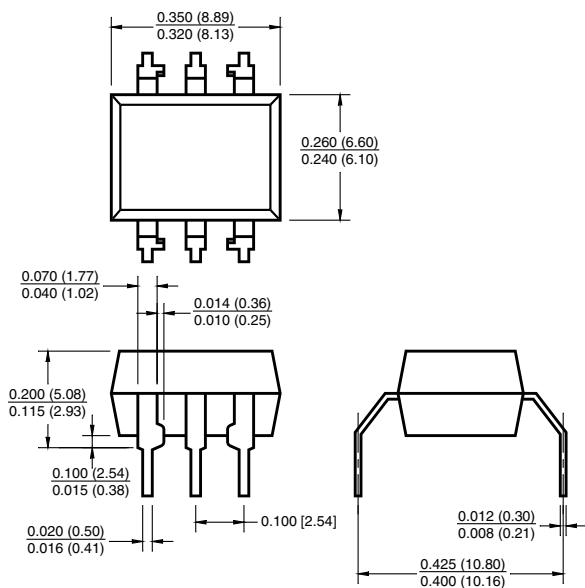
Through Hole



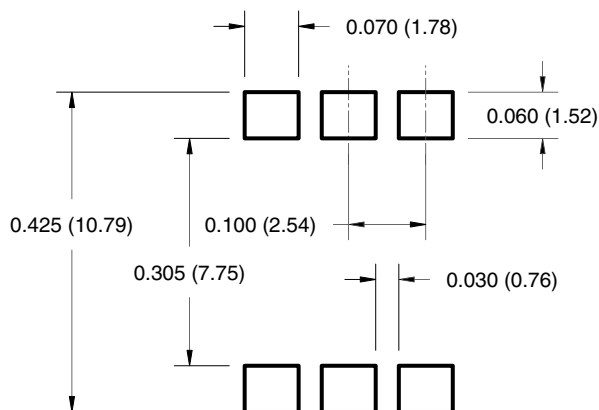
Surface Mount



0.4" Lead Spacing



Recommended Pad Layout for Surface Mount Leadform



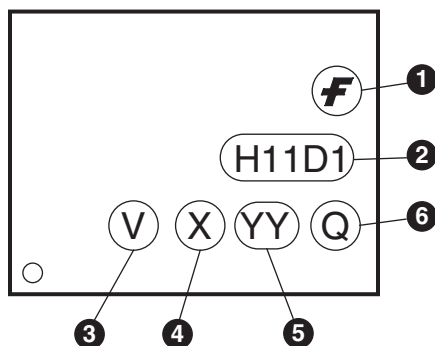
Note:

All dimensions are in inches (millimeters).

Ordering Information

Option	Order Entry Identifier (Example)	Description
No option	H11D1M	Standard Through Hole Device
S	H11D1SM	Surface Mount Lead Bend
SR2	H11D1SR2M	Surface Mount; Tape and Reel
T	H11D1TM	0.4" Lead Spacing
V	H11D1VM	VDE 0884
TV	H11D1TVM	VDE 0884, 0.4" Lead Spacing
SV	H11D1SVM	VDE 0884, Surface Mount
SR2V	H11D1SR2VM	VDE 0884, Surface Mount, Tape and Reel

Marking Information



Definitions	
1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code, e.g., '7'
5	Two digit work week ranging from '01' to '53'
6	Assembly package code

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